



Atty. Dkt. No. 039153-5003 (G0167)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Xiang, Qi
Title: SILICON BUFFERED
SHALLOW TRENCH
ISOLATION
Appl. No.: 10/755,746
Filing Date: 01/12/2004
Examiner: Steven W. Smoot
Art Unit: 2813
Conf. No.: 9599

CERTIFICATE OF EXPRESS MAILING
I hereby certify that this correspondence is being deposited with the United States Postal Service's "Express Mail Post Office To Addressee" service under 37 C.F.R. § 1.10 on the date indicated below and is addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

EV 828710917 US

5/23/07

(Express Mail Label Number)

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Carolyn Simpson

(Printed Name)

Carolyn Simpson

(Signature)

ISSUE FEE TRANSMITTAL

Mail Stop Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Enclosed herewith please find Issue Fee Transmittal Form PTOL-85(B).

A credit card payment form in the amount of \$1,700.00 for payment of the Issue Fee and the Publication Fee is also enclosed.

The Commissioner is hereby authorized to charge any additional fees which may be required regarding this application under 37 C.F.R. §§ 1.16-1.17, or credit any overpayment, to Deposit Account No. 19-0741. Should no proper payment be enclosed herewith, as by the credit card payment form being unsigned, providing incorrect information resulting in a rejected credit card transaction, or even entirely missing, the Commissioner is authorized to charge the unpaid amount to Deposit Account No. 19-0741.

Respectfully submitted,

Date 5/23/2007

By *MW Sprow*

FOLEY & LARDNER LLP
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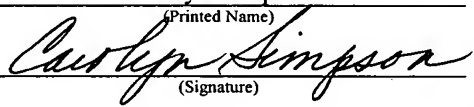
Marcus W. Sprow
Attorney for Applicant
Registration No. 48,580



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(Signature)	

COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

Mail Stop Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This communication is responsive to the Notice of Allowance dated February 28, 2007, concerning the above-referenced patent application.

The Examiner stated the following:

Claims 1-8 are allowed because the prior art of record does not teach or suggest, in combination with the other claim limitations, a method of manufacturing an integrated circuit having trench isolation regions in a substrate that includes the steps of providing a semiconductor or metal layer directly in contact with trench sidewalls such that the semiconductor layer or metal layer is in direct contact with a silicon-germanium layer and an overlying strained silicon layer and converting the semiconductor or metal layer into oxide liners corresponding to plural trenches;

Claims 9-16 are allowed because the prior art of record does not teach or suggest, in combination with the other claim limitations, a method of forming shallow trench isolation regions in a strained semiconductor layer that includes the steps of forming trenches in a strained semiconductor layer, providing a conformal semiconductor layer in the trenches in direct contact with the strained semiconductor layer, and

oxidizing the conformal semiconductor layer to form a liner in the trenches; and

Claims 17-18, 20 are allowed because the prior art of record does not teach or suggest, in combination with the other claim limitations, a method of forming a liner in a trench that includes the steps of providing a semiconductor layer in the trench such that the semiconductor layer is in direct contact with a germanium containing layer and an overlying strained layer and converting the semiconductor layer into an oxide liner such that substantially all of the semiconductor layer is consumed during the conversion.

While the Applicants agree that the allowed claims recite a combination of subject matter that is patentable over the cited references, the Applicants do not necessarily agree with or acquiesce in the statement of reasons for allowance given by the Examiner.

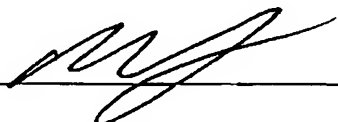
Moreover, the Applicants note that the recited subject matter as well as various other subject matter and/or combinations of subject matter may be patentable for other reasons than those given by the Examiner. The Applicants expressly reserve the right to set forth additional and/or alternative reasons for patentability and/or allowance in connection with the present Application or in any other future proceeding.

REMARKS

These Comments on Statement of Reasons for Allowance under 37 C.F.R. § 1.104 are intended to be responsive to the Notice of Allowance dated February 28, 2007.

Respectfully submitted,

Date 5/23/2007

By 

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